

IN THE CLAIMS:

Claims 10, 12, 19, and 20 have been cancelled. Claims 1-9, 11, 13, 14, 17, 18, 21-24, and 26 have been amended herein. Claims 27 and 28 have been added herein. All of the pending claims 1 through 28 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A method for forming a contact interface, comprising:
providing a substrate including semiconductor material with at least one contact comprising semiconductor material protruding from ~~said~~ the substrate;
forming a ~~first~~ layer comprising dielectric material over ~~said~~ the semiconductor material and ~~said~~ the at least one contact;
~~forming a second layer comprising polysilicon a silicide contact over said the first layer~~
comprising dielectric material and over at least a portion of a lateral surface of ~~said~~ the at least one contact; ~~and~~
~~forming a silicide contact at least an interface between said electrically conductive silicidable material and said second layer, including at said portion of said lateral surface.~~
2. (Currently Amended) The method of claim 1, wherein ~~said~~ forming ~~said~~ the first layer comprising dielectric material comprises forming silicon dioxide.
3. (Currently Amended) The method of claim ~~1~~ 27, further comprising:
forming a ~~third~~ layer comprising barrier material over ~~said~~ the ~~second~~ layer comprising polysilicon.
4. (Currently Amended) The method of claim 3, wherein ~~said~~ forming ~~said~~ the ~~third~~ layer comprising barrier material is effected before ~~said~~ forming ~~said~~ the silicide contact.

5. (Currently Amended) The method of claim 4, further comprising:
exposing at least a portion of ~~said the~~ second-layer comprising polysilicon located over ~~said the~~ at
least one contact, including at least a portion of ~~said the~~ second-layer comprising
polysilicon located over at least ~~said the~~ portion of ~~said the~~ lateral surface of ~~said the~~ at
least one contact through at least ~~said the~~ third-layer comprising barrier material.

6. (Currently Amended) The method of claim 3, wherein ~~said-forming~~ ~~said the~~ third
layer comprising barrier material comprises forming a layer comprising at least one of titanium
nitride, tungsten nitride, tungsten silicon nitride, and titanium silicon nitride.

7. (Currently Amended) The method of claim 3, further comprising forming ~~a fourth~~
another layer comprising dielectric material over ~~said the~~ second-layer comprising polysilicon
prior to ~~said-forming~~ ~~said the~~ third-layer comprising barrier material.

8. (Currently Amended) The method of claim 7, wherein ~~said-forming~~ ~~said the~~
fourth-layer comprising dielectric material comprises depositing TEOS.

9. (Currently Amended) The method of claim 7, wherein ~~said-forming~~ ~~said the~~
fourth-another layer comprising dielectric material comprises depositing silicon dioxide.

10. (Cancelled)

11. (Currently Amended) The method of claim ~~4~~27, wherein ~~said-disposing~~ forming
the layer comprising electrically conductive silicidable material comprises ~~disposing~~ forming a
layer comprising cobalt.

12. (Cancelled)

13. (Currently Amended) The method of claim ~~12~~27, wherein ~~said~~-annealing is effected by heating at least ~~said the semiconductor material~~ polysilicon to a temperature of about 400°C. to about 800°C.

14. (Currently Amended) The method of claim ~~12~~27, wherein ~~said~~-annealing is effected by heating at least ~~said the semiconductor material~~ polysilicon to a temperature of about 450°C. to about 600°C.

15. (Currently Amended) The method of claim 13, further comprising removing an unreacted portion of ~~said the~~ electrically conductive silicidable material.

16. (Currently Amended) The method of claim 15, wherein ~~said~~-removing ~~said the~~ unreacted portion is effected without substantially removing reacted electrically conductive silicidable material.

17. (Currently Amended) The method of claim ~~16~~28, wherein ~~said~~-removing ~~said the~~ unreacted portion is effected without substantially removing ~~said the~~ barrier material.

18. (Currently Amended) The method of claim 15, wherein ~~said~~-removing ~~said the~~ unreacted portion is effected ~~with an~~ with a hydrochloric/peroxide mixture solution.

19. (Cancelled)

20. (Cancelled)

21. (Currently Amended) The method of claim ~~20~~3, further including removing ~~said the third layer comprising barrier material~~ after ~~said~~-forming ~~said the~~ silicide contact.

22. (Currently Amended) The method of claim 21, wherein ~~said~~-removing ~~said the~~ third layer comprising barrier material is effected without substantially removing ~~said the~~ silicide contact.

23. (Currently Amended) The method of claim 22, wherein ~~said~~-removing ~~said the~~ third-layer comprising barrier material is effected without substantially removing ~~said the~~ first layer comprising dielectric material.

24. (Currently Amended) The method of claim 21, wherein ~~said~~-removing ~~said the~~ third-layer comprising barrier material comprises substantially completely removing ~~said the~~ barrier material.

25. (Currently Amended) The method of claim 21, wherein ~~said~~-removing is effected with an ammonia/peroxide mixture solution.

26. (Currently Amended) The method of claim 193, wherein ~~said~~-forming ~~said the~~ third-layer comprising barrier material comprises preventing ~~said the~~ electrically conductive silicidable material from reacting with ~~said the~~ semiconductor material through at least one of a void and an imperfection in ~~said the~~ first-layer comprising dielectric material.

27. (New) The method of claim 1, wherein forming the silicide contact comprises: forming a layer comprising polysilicon over the layer comprising dielectric material; and forming a layer comprising electrically conductive silicidable material over the layer comprising polysilicon; and annealing the polysilicon and the electrically conductive silicidable material.

28. (New) The method of claim 3, further comprising removing an unreacted portion of the electrically conductive silicidable material.